



HCD65T580-S

650V N-Channel Super Junction Power MOSFET

● Features:

■ 8.0A, 650V, $R_{DS(on)(Typ)} = 520m\Omega @ V_{GS}=10V$

■ Low Gate Charge

■ Low C_{rss}

■ 100% Avalanche Tested

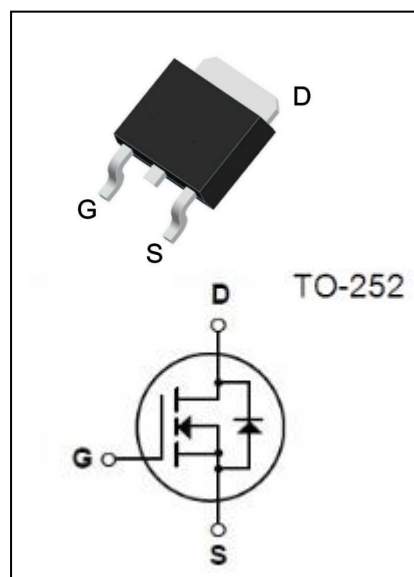
■ Fast Switching

■ Improved dv/dt Capability

● Application:

■ High Frequency Switching Mode Power Supply

■ Active Power Factor Correction



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-Source Voltage	650	V
I_D	Drain Current - Continuous($T_c=25^\circ\text{C}$) - Continuous($T_c=100^\circ\text{C}$)	8.0*	A
		5.06*	A
I_{DM}	Drain Current -Pulsed (Note1)	32*	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Limit Reference Value) (Note2)	88	mJ
I_{AR}	Avalanche Current (Note1)	2.0	A
E_{AR}	Repetitive Avalanche Energy (Note1)	2.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note3)	8.5	V/ns
P_D	Power Dissipation($T_C =25^\circ\text{C}$) -Derate above 25°C	82	W
		0.66	W/ $^\circ\text{C}$
T_j	Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to+150	$^\circ\text{C}$

* Drain Current Limited by Maximum Junction Temperature.

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Thermal Resistance,Junction to Case	1.52	$^\circ\text{C} / \text{W}$
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	69	$^\circ\text{C} / \text{W}$

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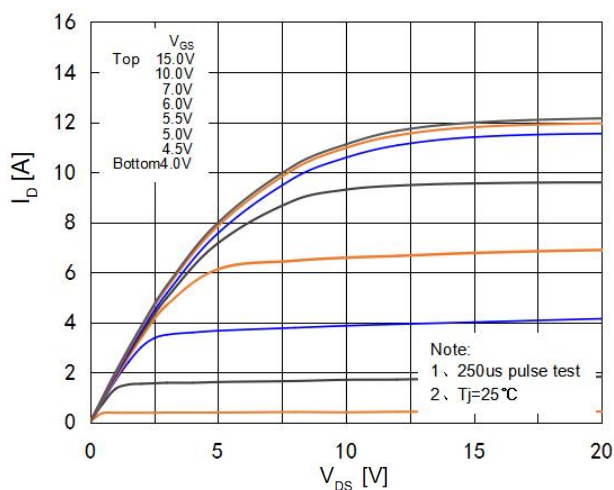
Electrical Characteristics(Tc=25°C unless otherwise noted)

Symbol	Parameter	Test Conditons	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-source Breakdown Voltage	V _{GS} =0V ,I _D =250μA	650	--	--	V
△BV _{DSS} /△T _J	Breakdown Voltage Temperature Coefficient	I _D =250μA (Referenced to 25°C)	--	0.60	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650V,V _{GS} =0V	--	--	1	μA
		V _{DS} =520V,Tc=125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current,Forward	V _{GS} =+30V, V _{DS} =0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current,Reverse	V _{GS} =-30V, V _{DS} =0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10 V, I _D =4.0A	--	520	580	mΩ
g _{FS}	Forward Transconductance	V _{DS} =20 V, I _D =4.0A (Note4)	--	4.4	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =50V,V _{GS} =0V, f=1.0MHz	--	481	--	pF
C _{oss}	Output Capacitance		--	29	--	pF
C _{rss}	Reverse Transfer Capacitance		--	1.6	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 325 V, I _D = 8.0 A, R _G = 25 Ω (Note4,5)	--	11	--	ns
t _r	Turn-On Rise Time		--	28	--	ns
t _{d(off)}	Turn-Off Delay Time		--	23	--	ns
t _f	Turn-Off Fall Time		--	24	--	ns
Q _g	Total Gate Charge	V _{DS} = 520 V, I _D =8.0 A, V _{GS} = 10 V (Note4,5)	--	12.5	--	nC
Q _{gs}	Gate-Source Charge		--	4.9	--	nC
Q _{gd}	Gate-Drain Charge		--	5.0	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	8.0	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	32	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0V,I _S =8.0 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =8.0 A, d I _F /dt=100A/μs (Note4)	--	219	--	ns
Q _{rr}	Reverse Recovery Charge		--	1.8	--	μC

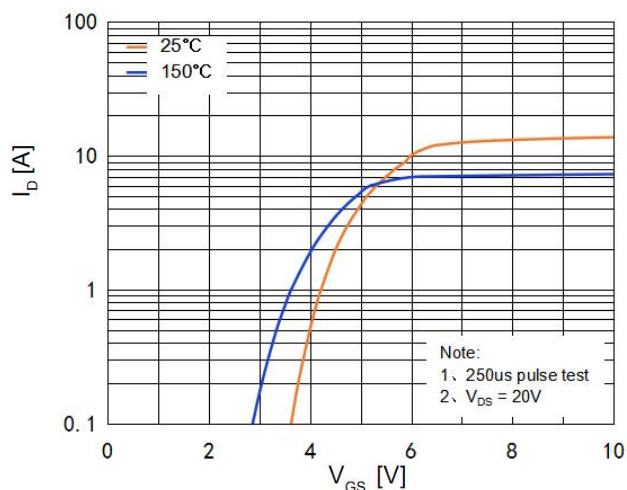
Notes:

- 1、Repetitive Rating:Pulse Width Limited by Maximum Junction Temperature.
- 2、L = 40mH, $I_{AS}=2.0A$, $V_{DD}=80V$, $R_G=25\Omega$, Starting $T_J=25^\circ C$.
- 3、 $I_{SD}\leq 8.0A$, $dI/dt\leq 200A/\mu s$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ C$.
- 4、Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 5、Essentially Independent of Operating Temperature.

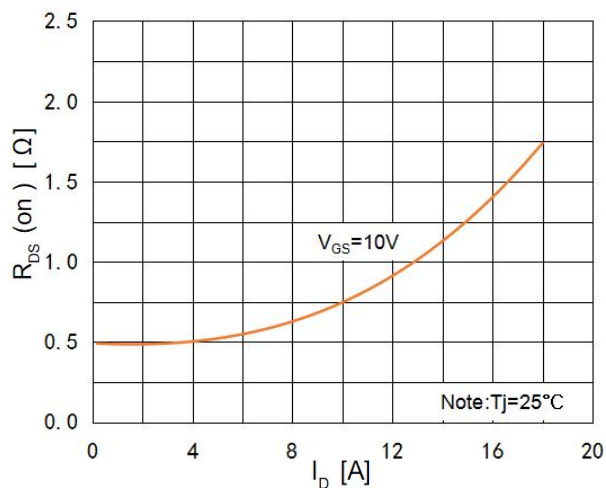
On-Regin Characteristics



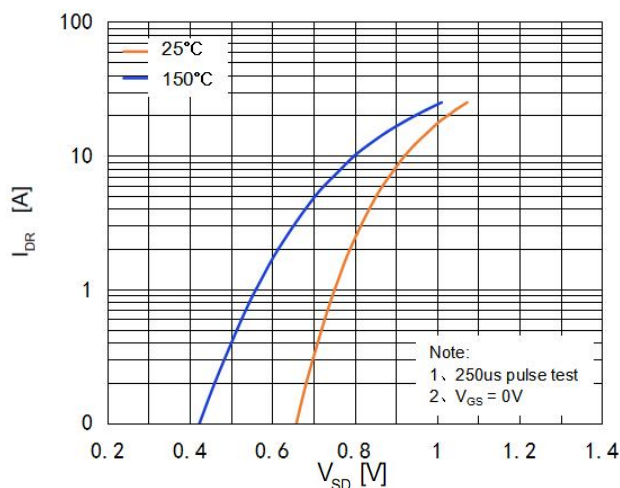
Transfer Characteristics



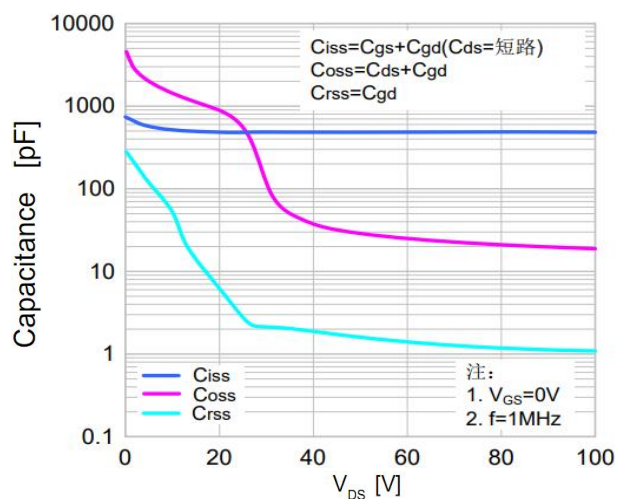
On-Resistance Variation vs. Drain Current and Gate Voltage



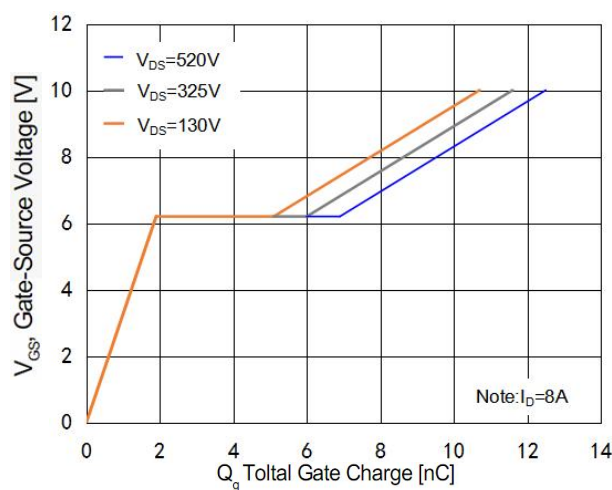
Body Diode Forward Voltage Variation vs. Source Current and Temperature



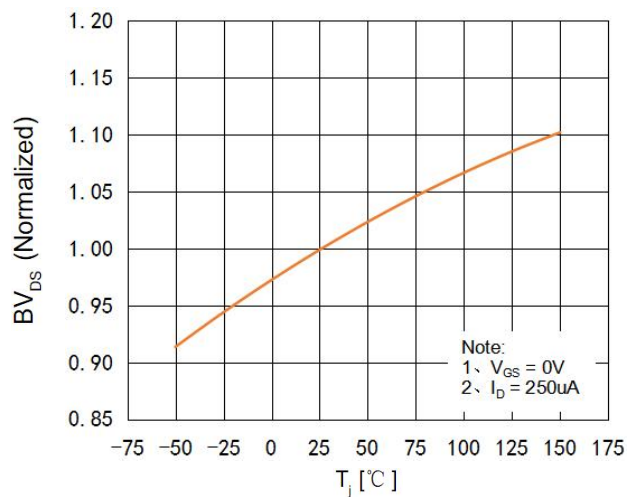
Capacitance Characteristics



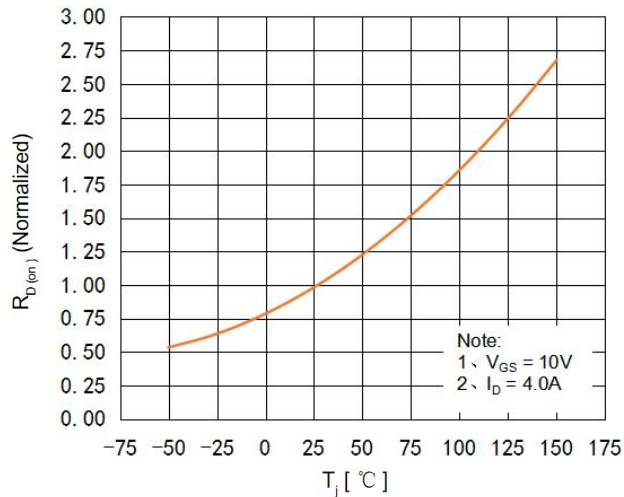
Gate Charge Characteristics



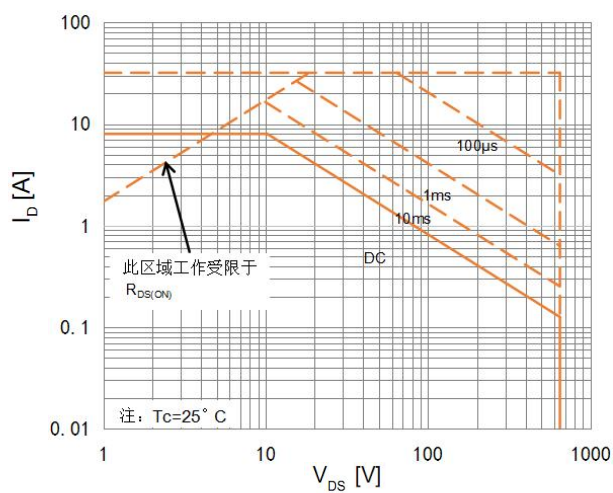
Breakdown Voltage Variation vs. Temperature



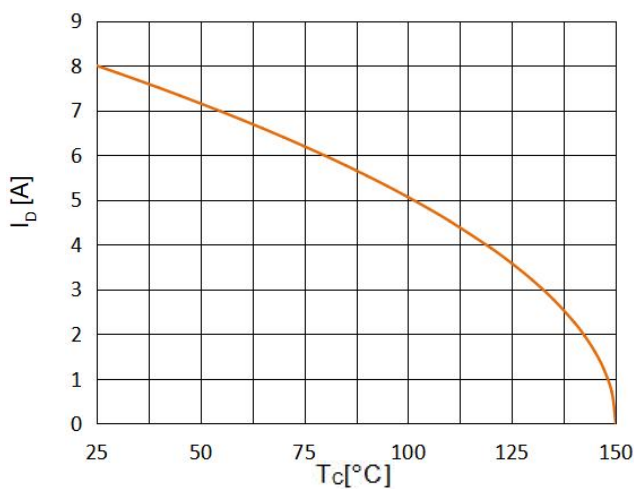
On-Resistance Variation vs. Temperature



Maximum Safe Operating Area



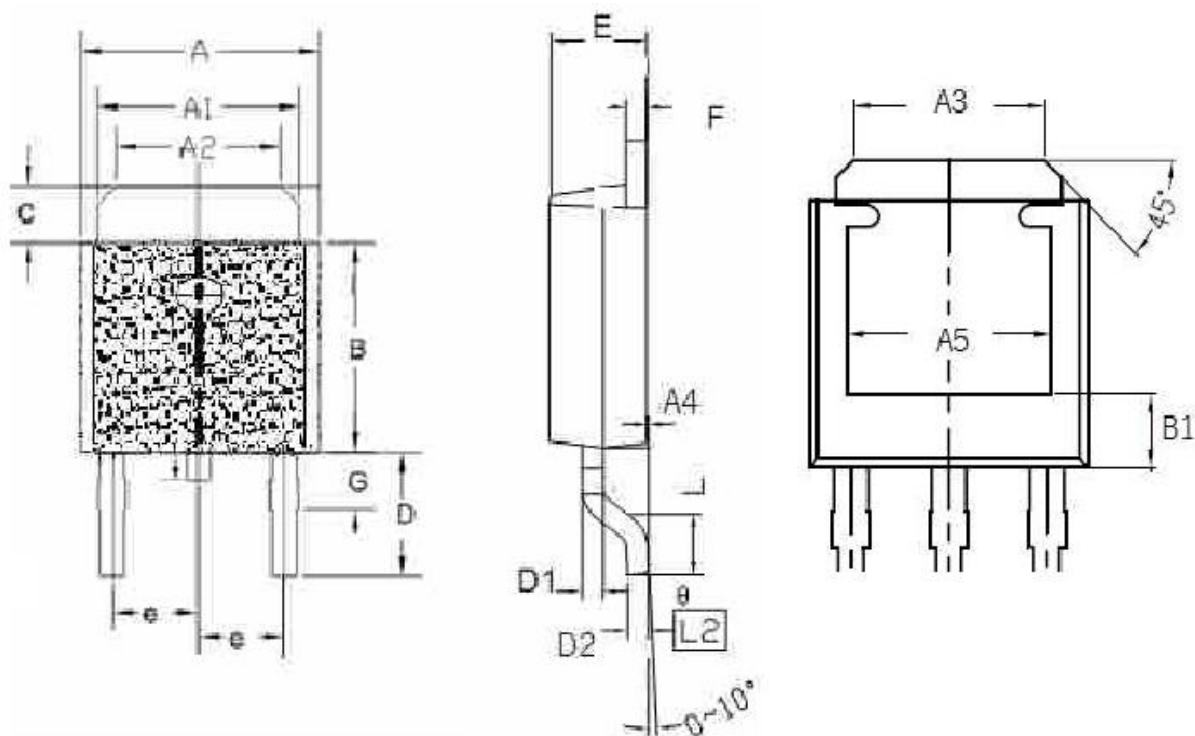
Maximum Drain Current Vs. Case Temperature



TO-252 Package Dimensions

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	6.40		6.60	D	2.90		3.10
A1	5.20		5.40	D1	0.45		0.55
A2	4.40		4.60	D2	0.45		0.55
A3	4.40		4.60	e		2.30	
A4	0		0.15	E	2.20		2.40
A5	4.65		4.95	F	0.45		0.55
B	5.90		6.20	G		1.70	
B1	1.57		1.77	L	1.40		1.60
C	0.90		0.96	θ (度)	0		10.00



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注意事项：

- 1、在电路设计时请不要超过器件的最大额定值，否则会影响整机的可靠性。
- 2、MOSFET产品为静电敏感型器件，使用时应注意采取防静电保护措施，如佩戴防静电手环、设备接地等。
- 3、如需安装散热片，请注意控制扭力大小及散热片的平整度。
- 4、该规格书由华科公司制作，并可能不定期更改，恕不另行通知。
- 5、如有疑问，请及时联系我司销售代表。

版本履历表：

序号	版本号	修改时间	修改记录
1	V1.0	2023-3-6	首次发行